

Silicon Diode

1N4249GP

1000V / 1A

DATASHEET

OEM – General Semiconductor

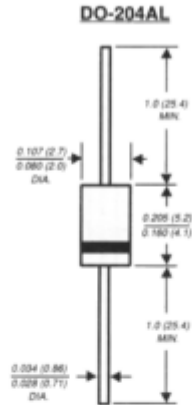
Source: General Semiconductor Databook 1998

1N4245GP THRU 1N4249GP

GLASS PASSIVATED JUNCTION RECTIFIER

Reverse Voltage - 200 to 1000 Volts Forward Current - 1.0 Ampere

PATENTED *



NOTE: Lead diameter is 0.026 (0.66) / 0.029 (0.74) for suffix "E" part numbers

Dimension in inches and (millimeters)

* Glass-plastic technique is covered by

Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306



FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ High temperature metallurgically bonded construction
- ◆ Glass passivated cavity-free junction
- ◆ Capable of meeting environmental standards of MIL-S-19500
- ◆ 1.0 Ampere operation at $T_A=55^\circ\text{C}$ with no thermal runaway
- ◆ High temperature soldering guaranteed: $350^\circ\text{C}/10$ seconds, $0.375"$ (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-204AL molded plastic over glass body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.012 ounce, 0.3 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	1N 4245GP	1N 4246GP	1N 4247GP	1N 4248GP	1N 4249GP	UNITS
* Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	800	1000	Volts
* Maximum RMS voltage	V_{RMS}	140	280	420	560	700	Volts
* Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	Volts
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=55^\circ\text{C}$	$I_{(AV)}$	1.0					Amp
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	25.0					Amps
* Maximum instantaneous forward voltage at 1.0A	V_F	1.2					Volts
* Maximum full load reverse current full cycle average 0.375" (9.5mm) lead length $T_A=55^\circ\text{C}$	$I_{R(AV)}$	50.0					μA
* Maximum reverse current at rated DC blocking voltage $T_A=25^\circ\text{C}$ $T_A=125^\circ\text{C}$	I_R	1.0 25.0					μA
Typical junction capacitance (NOTE 1)	C_J	8.0					pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$ $R_{\theta JL}$	55.0 25.0					$^\circ\text{C}/\text{W}$
* Operating junction temperature range	T_J	-65 to +160					$^\circ\text{C}$
* Storage temperature range	T_{STG}	-65 to +175					$^\circ\text{C}$

NOTES:

(1) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

(2) Thermal resistance from junction to ambient and from junction to lead at 0.375" (9.5mm) lead length, P.C.B. mounted

* JEDEC registered values

RATINGS AND CHARACTERISTIC CURVES 1N4245GP THRU 1N4249GP

